IN THE CLAIMS:

1-18. (Canceled)

19. (Previously Presented) An electroluminescence display apparatus comprising:

a first electrode formed above a substrate;

an emissive element layer formed on said first electrode;

a second electrode formed on said emissive element layer; and

a thickness of said first electrode is less than 1/2 a thickness of said emissive element layer, said thickness of said emissive element layer is approximately 200 nm.

20. (Previously Presented) An electroluminescence display apparatus comprising:

a first electrode formed above a substrate;

an emissive element layer formed on said first electrode;

a second electrode formed on said emissive element layer; and

a thickness of said first electrode is less than 1/3 a thickness of said emissive element layer, said thickness of said emissive element layer is approximately 200 nm.

21. (Previously Presented) An electroluminescence display apparatus comprising:

a first electrode formed above a substrate;

an emissive element layer formed on said first electrode;

a second electrode formed on said emissive element layer; and

a thickness of said first electrode is less than 1/2 a thickness of said emissive element layer, said thickness of said emissive element layer is approximately 200 nm, wherein

said electroluminescence display apparatus is an active-matrix type comprising said first electrode formed independently at each pixel, and thin-film transistor for driving said emissive element.

22. (Previously Presented) An electroluminescence display apparatus according to claim 21 further comprising the planarization insulating film formed so as to cover said thin-film transistor, with said first electrode formed on said planarization insulating film.

23. (Previously Presented) An electroluminescence display apparatus according to claim 21 wherein said emissive element layer comprises a layered structure of a hole transport layer, an emissive layer, and an electron transport layer.

24. (Previously Presented) An electroluminescence display apparatus comprising:

a first electrode formed above a substrate;

an emissive element layer formed on said first electrode;

a second electrode formed on said emissive element layer; and

a thickness of said first electrode is less than 1/2 a thickness of said emissive element layer, said thickness of said emissive element layer is approximately 200 nm, wherein

said electroluminescence display apparatus is a passive-matrix type wherein said first electrode extends in a first direction and said second electrode extends in a second direction so as to intersect said first electrode.

25. (Previously Presented) An electroluminescence display apparatus according to claim 24 wherein said emissive element layer comprises a layered structure of a hole transport layer, an emissive layer, and an electron transport layer.

26. (Currently Amended) An electroluminescence display apparatus comprising:

a first electrode formed above a substrate;

an emissive element layer formed on said first electrode, the emissive element layer comprises an organic layer that includes at least organic emissive molecules;

a second electrode formed on said emissive element layer; ~~and~~

a thickness of said first electrode is less than 1/2 the thickness of said emissive element layer.; and

wherein said first electrode is formed independently at each pixel;

each pixel comprises a thin film transistor for driving said emissive element layer; and

a planarization insulating film is formed so as to cover said thin film transistor, with said first electrode being formed on said planarization insulating film.

27. (Currently Amended) An electroluminescence display apparatus comprising:

a first electrode formed above a substrate;

an emissive element layer formed on said first electrode, the emissive element layer comprises an organic layer that includes at least organic emissive molecules;

a second electrode formed on said emissive element layer; ~~and~~

a thickness of said first electrode is less than 1/3 a thickness of said emissive element layer.; and

wherein said first electrode is formed independently at each pixel;

each pixel comprises a thin film transistor for driving said emissive element layer; and

a planarization insulating film is formed so as to cover said thin film transistor, with said first electrode being formed on said planarization insulating film.

28-29. (Canceled)